

What is claimed is:

1 1. A pixel structure of an active matrix organic
2 light emitting diode (OLED) display, comprising:

3 a first transistor having a gate terminal coupled to
4 a scan signal and a drain terminal coupled to a
5 data signal, the first transistor switching the
6 transmission of the data signal according to
7 the scan signal;

8 a storage capacitor having two terminals coupled to
9 a source terminal of the first transistor and a
10 reference node, the reference node having a
11 second voltage;

12 a second transistor having a gate terminal coupled
13 to the source terminal of the first transistor
14 and a source terminal coupled to the reference
15 node; and

16 an OLED having a cathode coupled to a drain terminal
17 of the second transistor and an anode coupled
18 to a first voltage exceeding the second
19 voltage;

20 wherein the first transistor or the second
21 transistor is an amorphous silicon thin film
22 transistor (a-Si TFT), and a light efficiency
23 of the OLED is no less than 11cd/A.

1 2. The pixel structure as claimed in claim 1,
2 wherein the OLED is made of C545T.

1 3. The pixel structure as claimed in claim 1,
2 wherein the OLED is made of Irppy.

1 4. The pixel structure as claimed in claim 1,
2 wherein the second voltage is a ground.

1 5. An active matrix organic light emitting diode
2 (OLED) display, comprising:

3 a panel, comprising a plurality of pixels, each
4 pixel comprising a first transistor having a
5 gate terminal coupled to a scan signal and a
6 drain terminal coupled to a data signal, the
7 first transistor switching the transmission of
8 the data signal according to the scan signal; a
9 storage capacitor having two terminals coupled
10 to a source terminal of the first transistor
11 and a reference node, the reference node having
12 a second voltage; a second transistor having a
13 gate terminal coupled to the source terminal of
14 the first transistor and a source terminal
15 coupled to the reference node; and an OLED
16 having a cathode coupled to a drain terminal of
17 the second transistor and an anode coupled to a
18 first voltage, the first voltage exceeding the
19 second voltage; wherein the first transistor or
20 the second transistor is an amorphous silicon
21 thin film transistor (a-Si TFT), and a light
22 efficiency of the OLED is no less than 11cd/A.

1 6. The pixel structure as claimed in claim 5,
2 wherein the OLED is made of C545T.

1 7. The pixel structure as claimed in claim 5,
2 wherein the OLED is made of Irppy.

1 8. The pixel structure as claimed in claim 5,
2 wherein the second voltage is a ground.

1 9. A pixel structure of an active matrix organic
2 light emitting diode (OLED) display, comprising:

3 a first transistor having a gate terminal coupled to
4 a scan signal and a drain terminal coupled to a
5 data signal, the first transistor switching the
6 transmission of the data signal according to
7 the scan signal;

8 a storage capacitor having two terminals coupled to
9 a source terminal of the first transistor and a
10 reference node, the reference node having a
11 second voltage;

12 a second transistor having a gate terminal coupled
13 to the source terminal of the first transistor
14 and a drain terminal coupled to the reference
15 node; and

16 an OLED having an anode coupled to a source terminal
17 of the second transistor and a cathode coupled
18 to a first voltage less than the second
19 voltage;

20 wherein the first transistor or the second
21 transistor is an amorphous silicon thin film
22 transistor (a-Si TFT), and a light efficiency
23 of the OLED is no less than 11cd/A.

1 10. The pixel structure as claimed in claim 9,
2 wherein the OLED is made of C545T.

1 11. The pixel structure as claimed in claim 9,
2 wherein the OLED is made of Irppy.

1 12. The pixel structure as claimed in claim 9,
2 wherein the second voltage is a high voltage.

1 13. An active matrix organic light emitting diode
2 (OLED) display, comprising:

3 a panel, comprising a plurality of pixels, each
4 pixel comprising a first transistor having a
5 gate terminal coupled to a scan signal and a
6 drain terminal coupled to a data signal, the
7 first transistor switching the transmission of
8 the data signal according to the scan signal; a
9 storage capacitor having two terminals coupled
10 to a source terminal of the first transistor
11 and a reference node, the reference node having
12 a second voltage; a second transistor having a
13 gate terminal coupled to the source terminal of
14 the first transistor and a drain terminal
15 coupled to the reference node; and an OLED
16 having an anode coupled to a source terminal of
17 the second transistor and a cathode coupled to
18 a first voltage less than the second voltage;
19 wherein the first transistor or the second
20 transistor is an amorphous silicon thin film
21 transistor (a-Si TFT), and a light efficiency
22 of the OLED is no less than 11cd/A.

1 14. The pixel structure as claimed in claim 13,
2 wherein the OLED is made of C545T.

1 15. The pixel structure as claimed in claim 13,
2 wherein the OLED is made of Irppy.

1 16. The pixel structure as claimed in claim 13,
2 wherein the second voltage is a high voltage.